VNDQ06

Siliconix incorporated

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

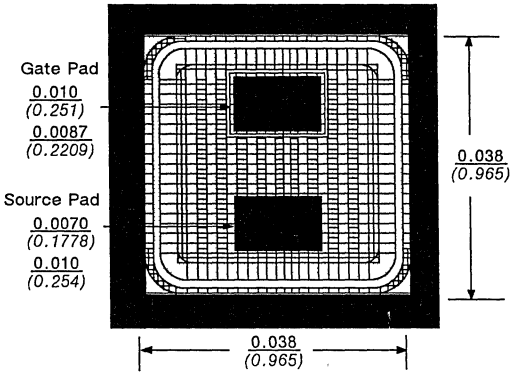
- Switching
- Amplification

FEATURES

- Low $r_{DS(on)}$ < 3.5 Ω

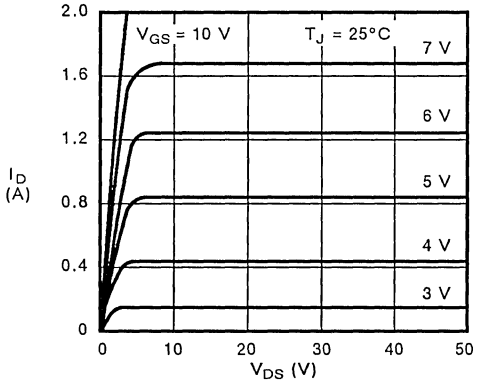
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• 2N6659, 2N6660 VN67AB
	TO-220SD	• VN40AFD, VN46AFD, VN66AFD, VN67AFD
	TO-220	• VN66AD, VN67AD
Quad	14-Pin Plastic	• VQ1004J
	14-Pin Dual-In-Line	• VQ1004P
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

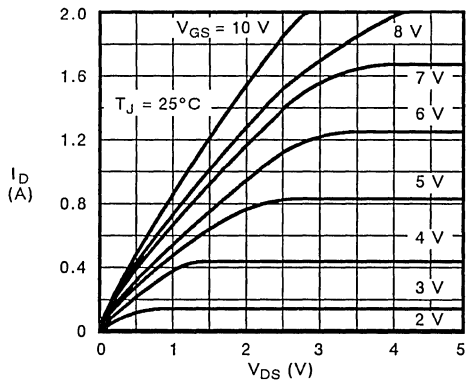


TYPICAL CHARACTERISTICS

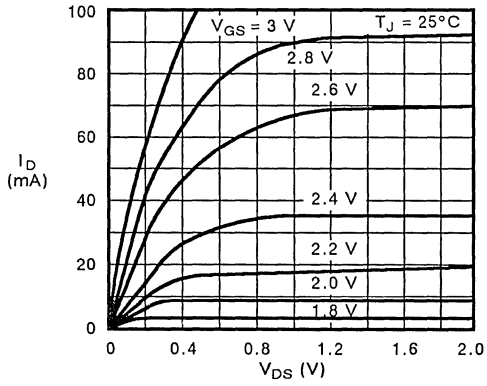
Output Characteristics



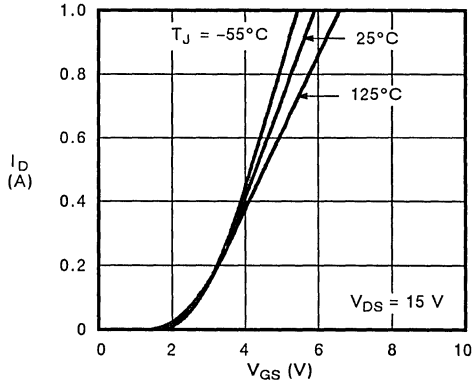
Ohmic Region Characteristics



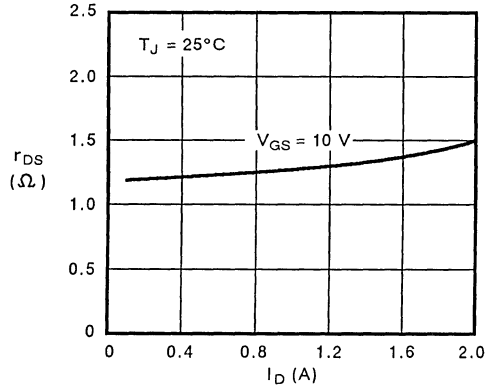
Output Characteristics for Low Gate Drive



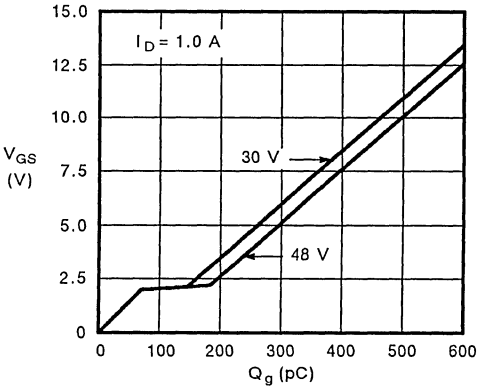
Transfer Characteristics



On-Resistance



Gate Charge



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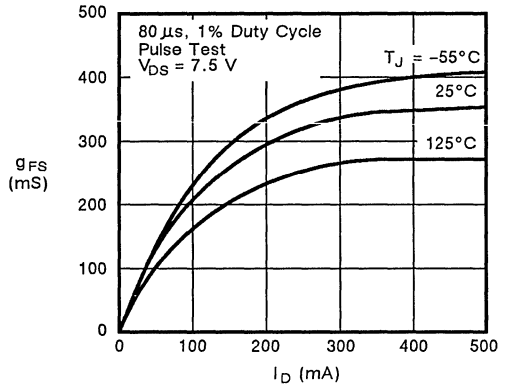
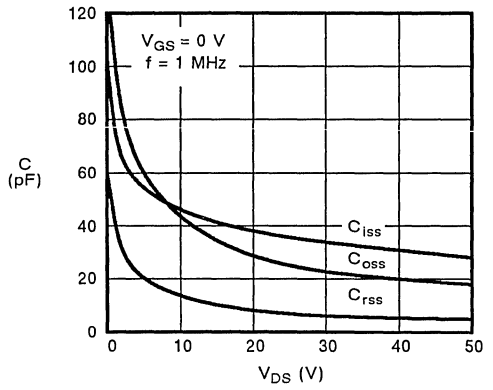
TYPICAL CHARACTERISTICS

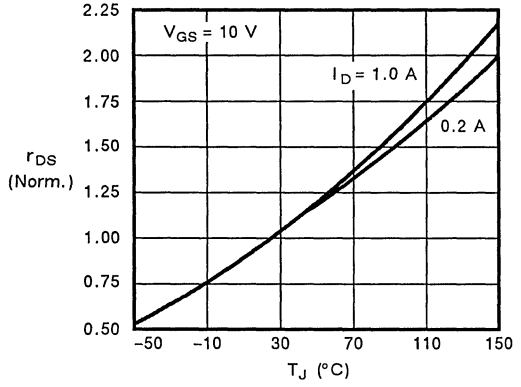
Transconductance



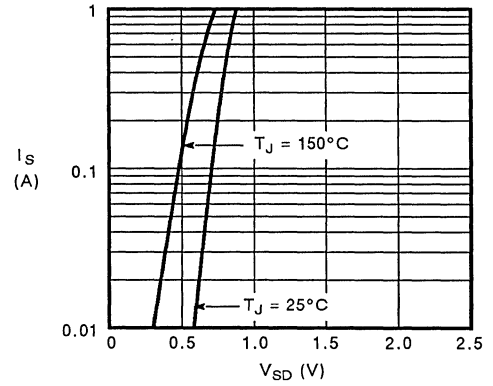
Capacitance



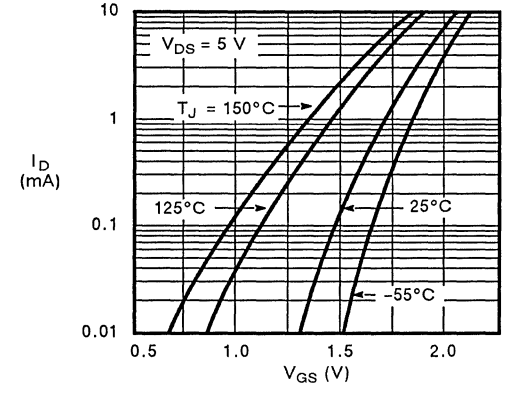
On-Resistance vs. Junction Temperature



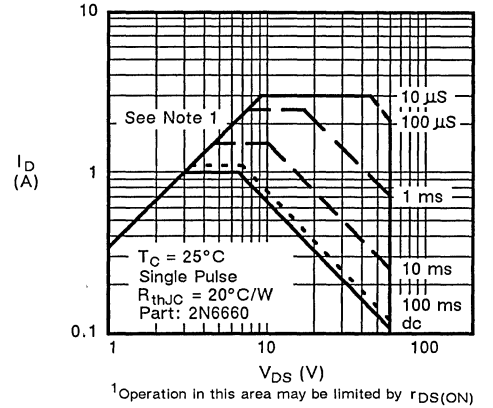
Source-Drain Diode Forward Voltage



Threshold Region



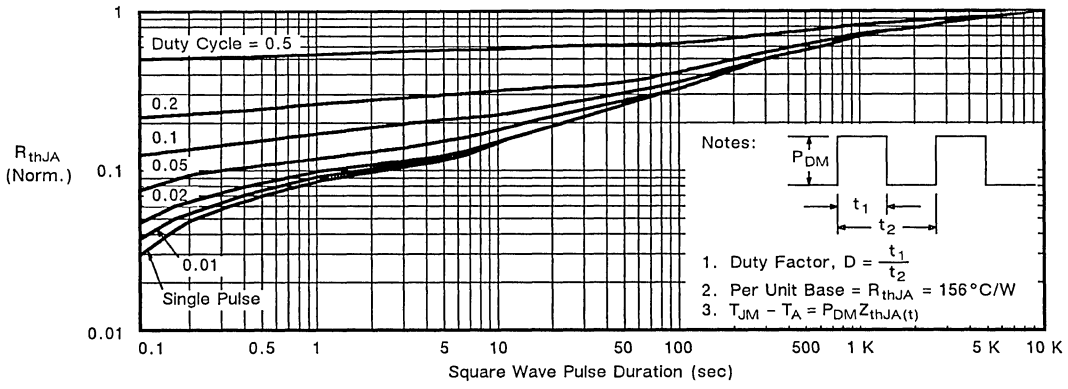
Safe Operating Area



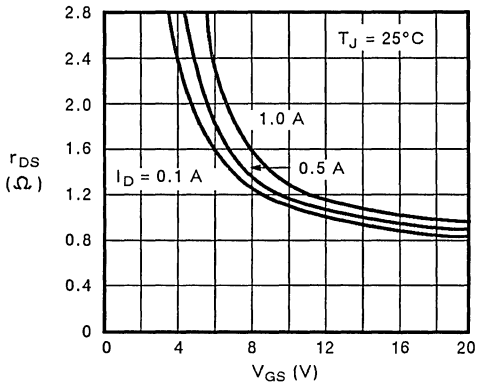
[1]Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

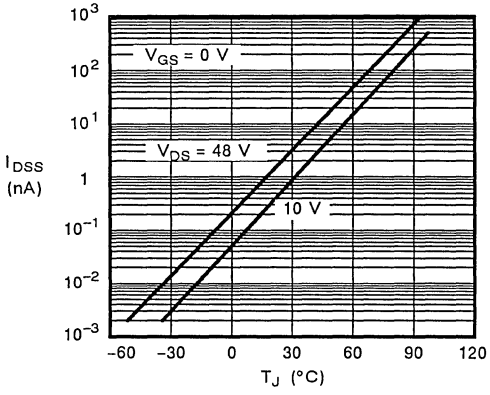
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



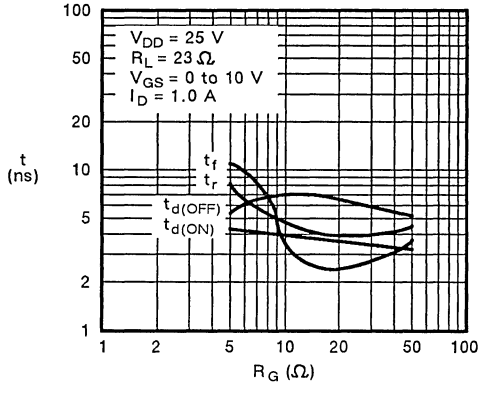
On-Resistance vs. Gate to Source Voltage



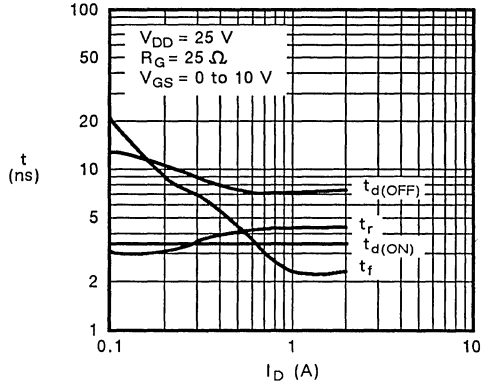
Off State Current



Drive Resistance Effects on Switching



Load Condition Effects on Switching



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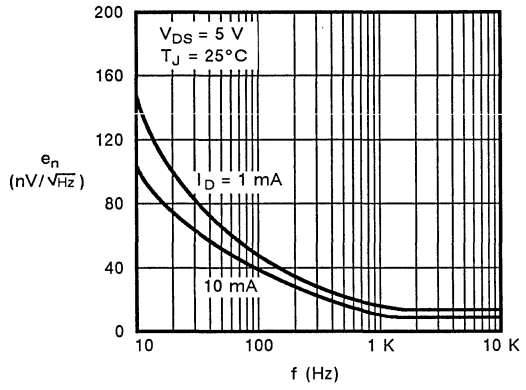
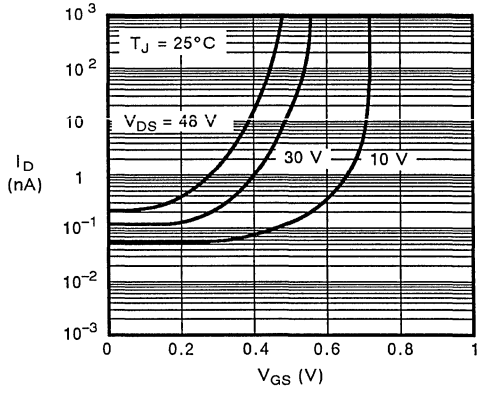
TYPICAL CHARACTERISTICS

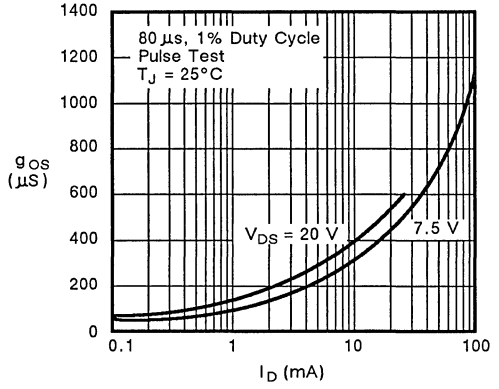
Equivalent Input Noise Voltage vs. Frequency



Body-Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-205AD)